

General Description

The CMSA1482 uses advanced trench technology to provide excellent RDS (ON), This device is ideal for boost converters and synchronous rectifiers for consumer, telecom, industrial power supplies and LED backlighting.

Features

- Low On-Resistance
- 100% avalanche tested
- Small Footprint (5x6 mm) for Compact Design
- RoHS Compliant

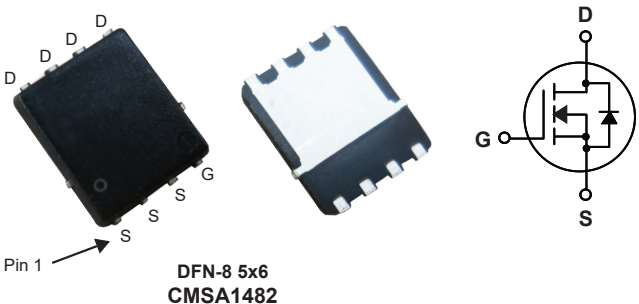
Product Summary

BVDSS	R _{DS(on)} max.	ID
100V	35mΩ	30A

Applications

- DC-DC Converter
- Motor Drive
- Powertrain Management

DFN-8 5x6 Pin Configuration



Absolute Maximum Ratings

Symbol	Parameter	Rating	Units
V _{DS}	Drain-Source Voltage	100	V
V _{GS}	Gate-Source Voltage	±20	V
I _D @T _C =25°C	Continuous Drain Current	30	A
I _D @T _C =100°C	Continuous Drain Current	21	A
I _{DM}	Pulsed Drain Current	120	A
EAS	Single Pulse Avalanche Energy ¹	144	mJ
P _D @T _C =25°C	Total Power Dissipation	75	W
T _{STG}	Storage Temperature Range	-55 to 150	°C
T _J	Operating Junction Temperature Range	-55 to 150	°C

Thermal Data

Symbol	Parameter	Typ.	Max.	Unit
R _{θJA}	Thermal Resistance, Junction-to-Ambient	---	65	°C/W
R _{θJC}	Thermal Resistance Junction -Case	---	2	°C/W

N-Channel Enhancement Mode Field Effect Transistor

Electrical Characteristics ($T_J=25^{\circ}\text{C}$, unless otherwise noted)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV_{DS}	Drain-Source Breakdown Voltage	$V_{GS}=0V$, $I_D=250\mu A$	100	---	---	V
$R_{DS(ON)}$	Static Drain-Source On-Resistance	$V_{GS}=10V$, $I_D=10A$	---	---	35	m Ω
		$V_{GS}=4.5V$, $I_D=10A$	---	---	40	
$V_{GS(th)}$	Gate Threshold Voltage	$V_{GS}=V_{DS}$, $I_D=250\mu A$	1	---	2.5	V
I_{DSS}	Drain-Source Leakage Current	$V_{DS}=80V$, $V_{GS}=0V$	---	---	1	μA
I_{GSS}	Gate-Source Leakage Current	$V_{GS}=\pm 20V$, $V_{DS}=0V$	---	---	± 100	nA
g_{fs}	Forward Transconductance	$V_{DS}=10V$, $I_D=7A$	---	20	---	S
R_g	Gate Resistance	$V_{DS}=0V$, $V_{GS}=0V$, $f=1MHz$	---	2	---	Ω
Q_g	Total Gate Charge	$V_{DS}=50V$, $I_D=6.5A$ $V_{GS}=10V$	---	60	---	nC
Q_{gs}	Gate-Source Charge		---	9	---	
Q_{gd}	Gate-Drain Charge		---	13	---	
$T_{d(on)}$	Turn-On Delay Time	$V_{DS}=50V$, $V_{GS}=10V$, $I_D=6.5A$ $R_{G_ext}=2.7\Omega$	---	10	---	ns
T_r	Rise Time		---	26	---	
$T_{d(off)}$	Turn-Off Delay Time		---	44	---	
T_f	Fall Time		---	55	---	
C_{iss}	Input Capacitance	$V_{DS}=25V$, $V_{GS}=0V$, $f=1MHz$	---	2700	---	pF
C_{oss}	Output Capacitance		---	130	---	
C_{rss}	Reverse Transfer Capacitance		---	100	---	

Diode Characteristics

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
I_S	Diode continuous forward current	$V_G=V_D=0V$, Force Current	---	---	30	A
$I_{S,pulse}$	Diode pulse current		---	---	120	A
V_{SD}	Diode Forward Voltage	$V_{GS}=0V$, $I_F=10A$, $T_J=25^{\circ}\text{C}$	---	0.81	1.2	V

Notes:

1.The EAS data shows Max. rating .The test condition is $V_{DS}=50V$, $V_{GS}=10V$, $L=0.5mH$, $I_{AS}=24A$.

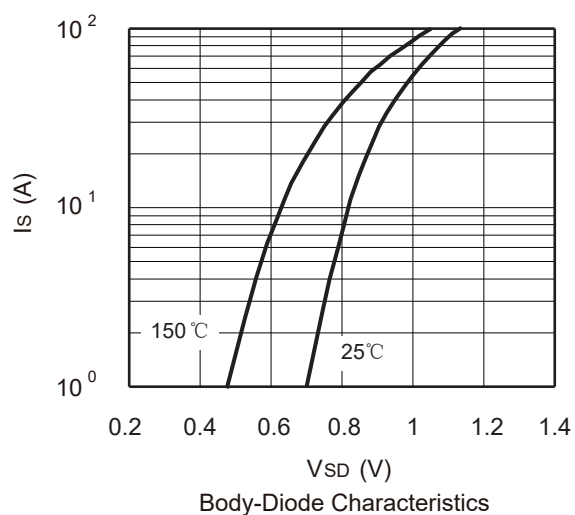
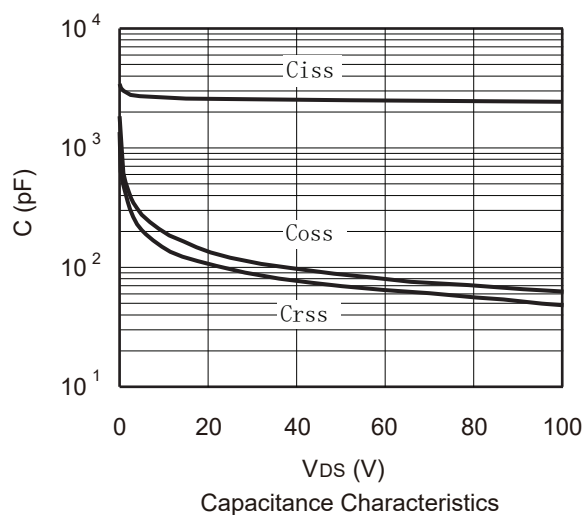
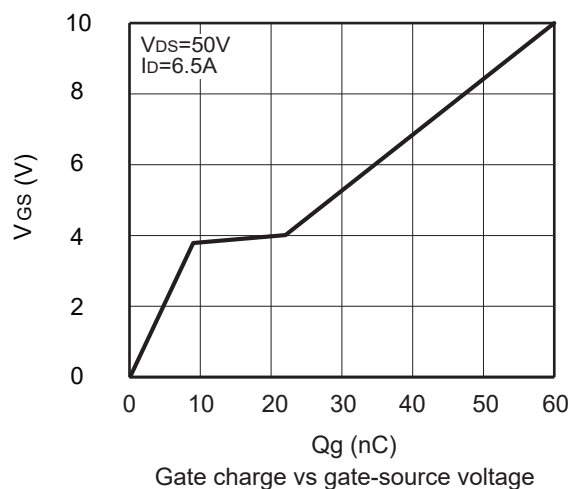
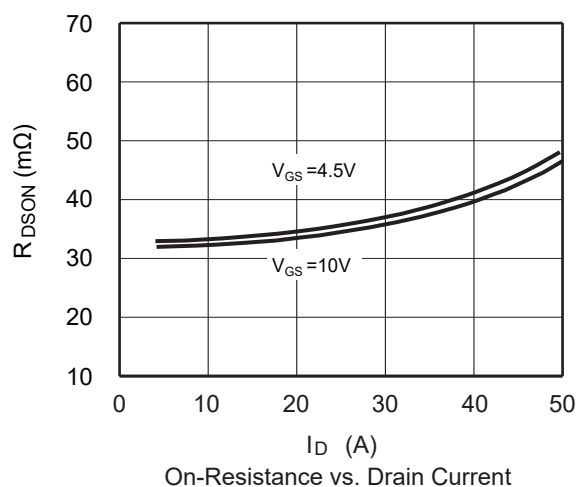
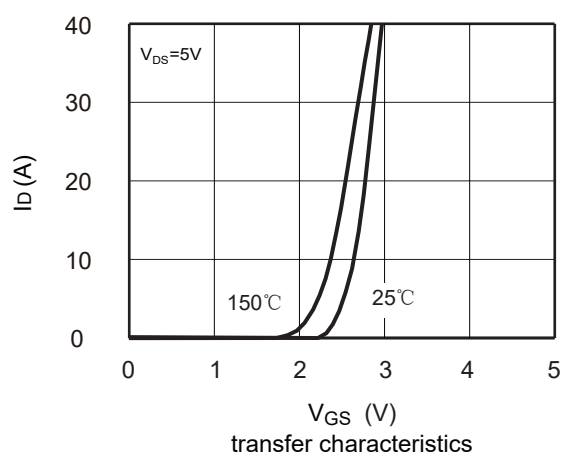
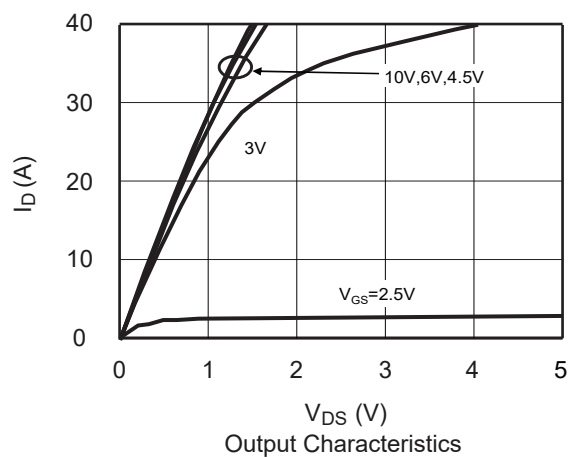
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Cmos reserves the right to improve product design ,functions and reliability without notice.Please refer to the latest version of specification.

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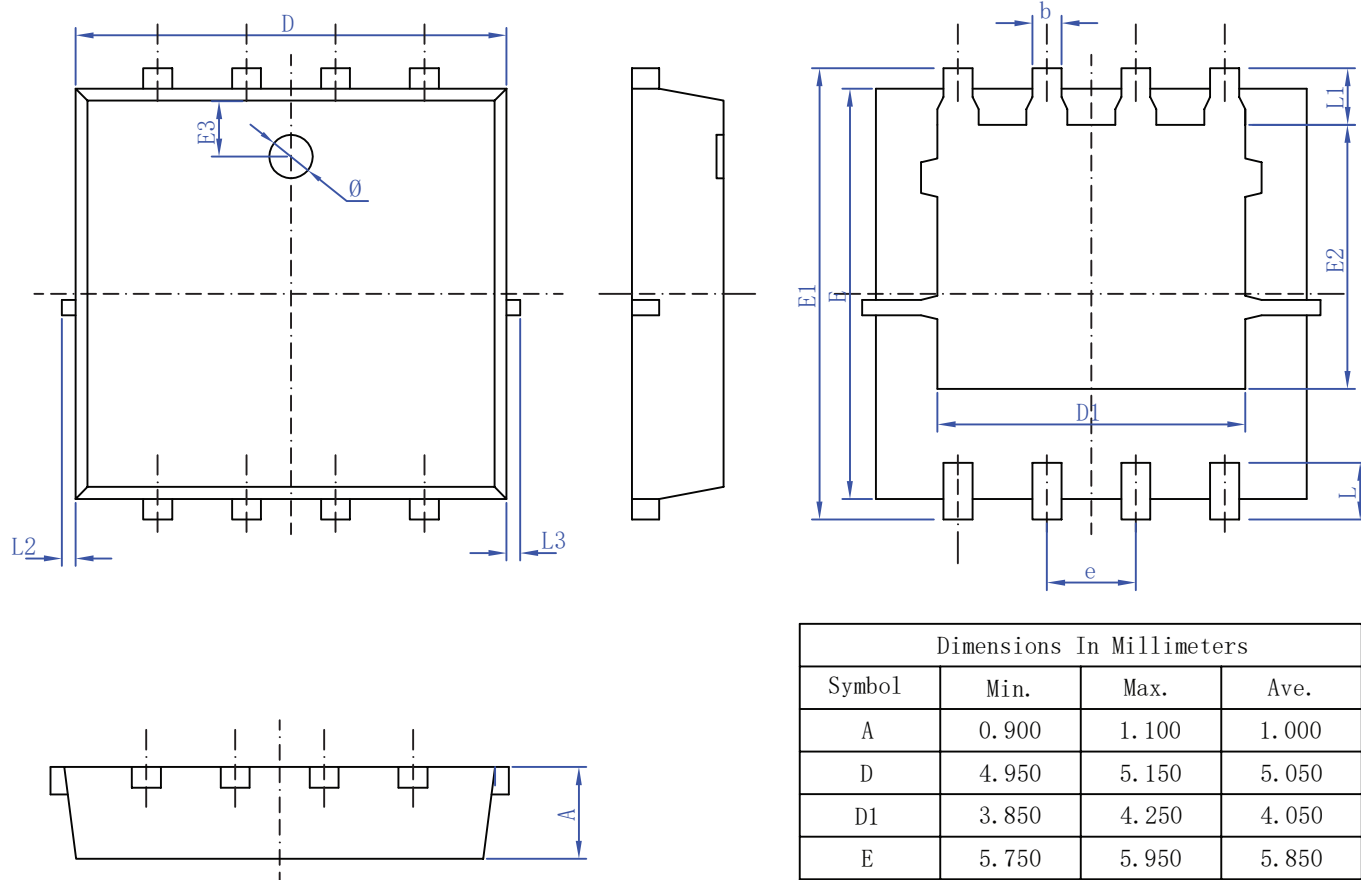
Typical Characteristics



Package Dimension

DFN-8 5x6

Unit :mm



注:

1. 未注公差 ± 0.05 未标注圆角 $R_{\max} = 0.25$

Dimensions In Millimeters			
Symbol	Min.	Max.	Ave.
A	0.900	1.100	1.000
D	4.950	5.150	5.050
D1	3.850	4.250	4.050
E	5.750	5.950	5.850
E1	5.950	6.350	6.150
E2	3.300	3.700	3.500
E3	0.900	1.300	1.100
b	0.250	0.350	0.300
e	1.220	1.320	1.270
L	0.585	0.785	0.685
L1	0.525	0.725	0.625
Ø	1.000	1.400	1.200
L2	0~0.100		
L3	0~0.100		